

DATA INPUT CIRCUIT AND METHOD
FOR SYNCHRONOUS SEMICONDUCTOR MEMORY DEVICE

ABSTRACT OF THE DISCLOSURE

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A circuit for receiving data to be written in a synchronous semiconductor memory device, comprising: a first set of latches for receiving an n-bit data upon transition of an internal strobe signal; a counter for counting the number of transitions of the internal strobe signal and for outputting an indicating signal upon counting the end of a string of internal strobe signals; a second set of latches for receiving the outputs of the first set of latches, the second set of latches being clocked by the indicating signal; and a third set of latches for receiving the outputs of the second set of latches, the third set of latches being clocked by a clock signal derived from a system clock.

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